

## MS48N40

### N-Channel 40-V (D-S) MOSFET

#### Description

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $R_{DS(on)}$  and to ensure minimal power loss and heat dissipation.

Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, and PCMCIA cards, cellular and cordless telephones.

#### Features

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Miniature SO-8 surface mount package saves board space
- High power and current handling capability
- Low side high current DC-DC Converter applications
- RoHS compliant package

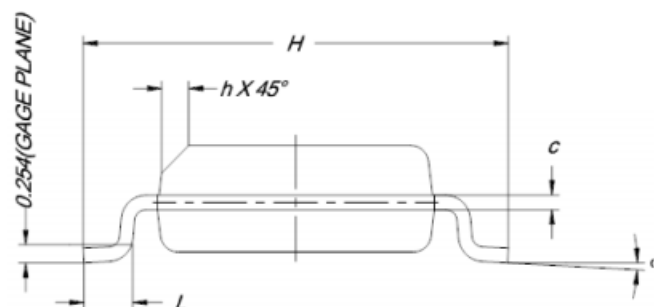
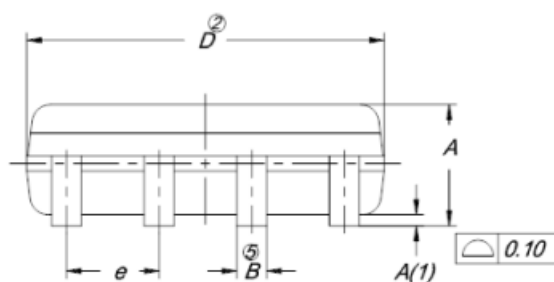
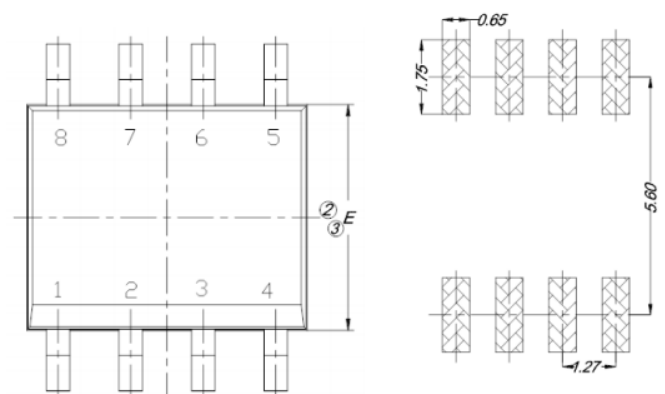
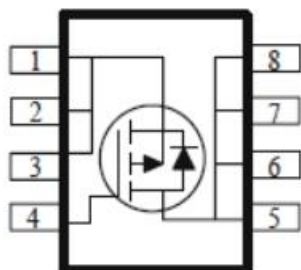
#### Packing & Order Information

3,000/Reel



**RoHS**  
COMPLIANT

#### Graphic symbol



| DIM.     | MILLIMETERS |      |      |
|----------|-------------|------|------|
|          | MIN.        | NOM. | MAX. |
| A        | 1.35        | 1.55 | 1.75 |
| A(1)     | 0.10        | 0.18 | 0.25 |
| B        | 0.38        | 0.45 | 0.51 |
| C        | 0.19        | 0.22 | 0.25 |
| D        | 4.80        | 4.90 | 5.00 |
| E        | 3.80        | 3.90 | 4.00 |
| e        | 1.27 BSC    |      |      |
| H        | 5.80        | 6.00 | 6.20 |
| L        | 0.50        | 0.72 | 0.93 |
| $\alpha$ | 0°          | 4°   | 8°   |
| h        | 0.25        | 0.38 | 0.50 |

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#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

##### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

| Symbol        | Parameter  | Value       | Unit               |
|---------------|--|-------------|--------------------|
| $V_{DS}$      | Drain-Source Voltage   | 40          | V                  |
| $V_{GS}$      | Gate-Source Voltage  | $\pm 20$    | V                  |
| $I_D$         | Continuous Drain Current <sup>a</sup> ( $T_A=25^{\circ}\text{C}$ ) | $\pm 9.7$   | A                  |
|               | Continuous Drain Current <sup>a</sup> ( $T_A=70^{\circ}\text{C}$ ) | $\pm 7.2$   | A                  |
| $I_{DM}$      | Pulsed Drain Current <sup>b</sup>                                  | $\pm 50$    | A                  |
| $I_S$         | Continuous Source Current (Diode Conduction) <sup>a</sup>          | 2.3         | A                  |
| $P_D$         | Power Dissipation <sup>a</sup> ( $T_A=25^{\circ}\text{C}$ )        | 3.1         | W                  |
|               | Power Dissipation <sup>a</sup> ( $T_A=70^{\circ}\text{C}$ )        | 2.2         | W                  |
| $T_J/T_{STG}$ | Operating Junction and Storage Temperature                         | -55 to +150 | $^{\circ}\text{C}$ |

##### Thermal Resistance Ratings

| Symbol          | Parameter   | Maximum | Units                |
|-----------------|---|---------|----------------------|
| $R_{\theta JA}$ | Maximum Junction-to-Ambient <sup>a</sup> ( $t \leq 10$ sec) | 50      | $^{\circ}\text{C/W}$ |
|                 | Maximum Junction-to-Ambient <sup>a</sup> (Steady-State)     | 92      |                      |

##### Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.  
b. Pulse width limited by maximum junction temperature

##### Static

| Symbol       | Parameter                       | Test Conditions  | Min | Typ. | Max.      | Units         |
|--------------|---------------------------------|--|-----|------|-----------|---------------|
| $V_{GS(th)}$ | Gate-Threshold Voltage          | $V_{DS} = V_{GS}$ , $I_D = -250\mu\text{A}$  | 1   |      |           | V             |
| $I_{GSS}$    | Gate-Body Leakage               | $V_{DS} = 0$ V, $V_{GS} = 20$ V  |     |      | $\pm 100$ | nA            |
| $I_{DSS}$    | Zero Gate Voltage Drain Current | $V_{DS} = 24$ V, $V_{GS} = 0$ V<br>$V_{DS} = 24$ V, $V_{GS} = 0$ V, $T_J = 55^{\circ}\text{C}$ |     |      | 1<br>25   | $\mu\text{A}$ |
| $I_{D(on)}$  | On-State Drain Current          | $V_{DS} = 5$ V, $V_{GS} = 10$ V  | 20  |      |           | A             |
| $r_{DS(on)}$ | Drain-Source On-Resistance      | $V_{GS} = 10$ V, $I_D = 9.7$ A<br>$V_{GS} = 4.5$ V, $I_D = 8.8$ A                              |     |      | 22<br>27  | m $\Omega$    |
| $g_{fs}$     | Forward Transconductance        | $V_{DS} = 15$ V, $I_D = 9.7$ A   |     | 40   |           | S             |
| $V_{SD}$     | Diode Forward Voltage           | $I_S = 2.3$ A, $V_{GS} = 0$ V  |     | 0.7  |           | V             |

##### Dynamic<sup>b</sup>

| Symbol   | Parameter          | Test Conditions                                     | Min | Typ. | Max. | Units |
|----------|--------------------|---|-----|------|------|-------|
| $Q_g$    | Total Gate Charge  | $V_{DS} = 15$ V, $I_D = 9.7$ A,<br>$V_{GS} = 4.5$ V | --  | 12.5 | --   | nC    |
| $Q_{gs}$ | Gate-Source Charge |   | --  | 2.6  | --   | nC    |
| $Q_{gd}$ | Gate-Drain Charge  |   | --  | 4.6  | --   | nC    |

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| Dynamic <sup>b</sup> |                     |   |     |      |      |       |
|----------------------|---------------------|---|-----|------|------|-------|
| Symbol               | Parameter           | Test Conditions   | Min | Typ. | Max. | Units |
| $t_{d(on)}$          | Turn-On Delay Time  | $V_{DD} = 25\text{ V}$ , $R_L = 25\ \Omega$ ,<br>$V_{GEN} = 10\text{ V}$ , $I_D = 1\text{ A}$ | --  | 20   | --   | ns    |
| $t_r$                | Rise Time           |   | --  | 9    | --   | ns    |
| $t_{d(off)}$         | Turn-Off Delay Time |   | --  | 70   | --   | ns    |
| $t_f$                | Fall Time           |   | --  | 20   | --   | ns    |

**Notes:**

- a. Pulse test:  $PW \leq 300\mu s$  duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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